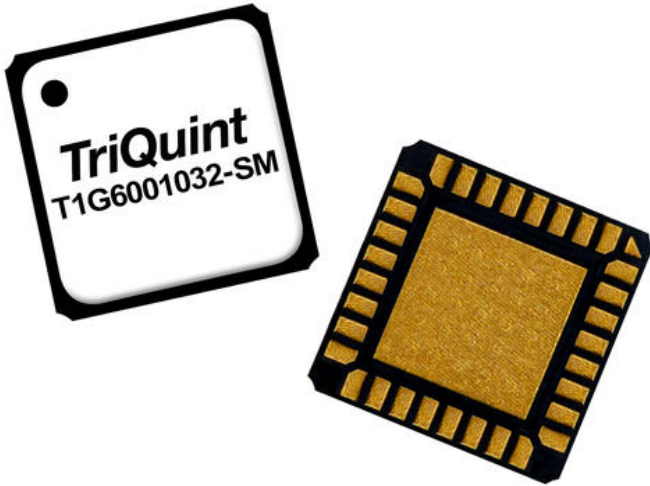


## RFMW to Support 10W GaN Transistor from TriQuint Semiconductor

WDD Staff



[RFMW](#) [1] announces design and sales support for the T1G6001032-SM, a ceramic packaged, 10W peak (P3dB) power transistor fabricated using [TriQuint Semiconductor](#) [2]'s proven Gallium Nitride (GaN) production process. Offering a broad instantaneous bandwidth afforded from TriQuint's TQGaN25 process technology, the T1G6001032-SM:

- Is rated from DC to 6GHz.
- Offers >17dB mid-band linear gain with over 50% efficiency.
- Operates at 32V with only 50mA of quiescent drain current, finding applications in commercial and military radar, communication transceivers, avionics, and wideband amplifier designs.
- Comes packaged in a ceramic, 5x5mm QFN for minimal thermal resistance and ease of use.

For more information please visit [rfmw.com](http://rfmw.com) [1]

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<http://www.wirelessdesignmag.com/product-releases/2013/09/rfmw-support-10w-gan-transistor-triquint-semiconductor>

### Links:

[1] <http://www.rfmw.com>

[2] <http://www.triquint.com>